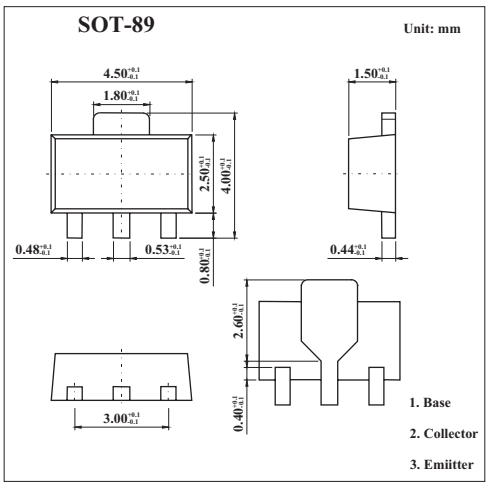
Power Transistor

2SA1797



■ Features

- Low saturation voltage. $V_{CE(sat)}$=-0.35V(Max.) at I_C / I_B=-1A/-50mA.
- Excellent DC current gain characteristics.
- Complements the 2SA1797 and 2SC4672.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-emitter Voltage	V_{CEO}	-50	V
Collector-base Voltage	V_{CBO}	-50	V
Emitter-base Voltage	V_{EBO}	-6	V
Collector current	I_C	-3	A
Collector power dissipation	P_C	0.5	W
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA	-50			V
Collector-base breakdown voltae	BV_{CBO}	I_C = -50 μ A	-50			V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -50 μ A	-6			V
Collector cutoff current	I_{CBO}	V_{CB} = -50V			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -5V			-0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -1A , I_B = -50mA		-0.15	-0.35	V
DC current transfer ratio	h_{FE}	V_{CE} = -2V , I_C = -0.5A	82		270	
Transition frequency	f_T	V_{CE} = -2V , I_E = 0.5A , f = 100MHz		200		MHz
Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0A , f = 1MHz		36		pF

■ h_{FE} Classification

Marking	AG	
Rank	P	Q
hFE	82～180	120～270